

Appln. No. 10/519,895
Amdt. Dated April 14, 2006
Reply to Office Action of December 29, 2005

AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A magnetic non-volatile memory device provided with a magnetic shielding structure for suppressing the influence of external magnetic fields, ~~said device characterized in that:~~

wherein a magnetic shield layer made from a soft magnetic metal is formed at a top and a bottom region ~~on a surface~~ of said device for suppressing penetration of magnetic flux into said device, ~~and~~

wherein said magnetic shield layers are formed ~~on a device surface~~ at the mounting side of said device, and on a device surface opposite to said mounting side of said device, and

wherein said device includes a plurality of layers between the magnetic shield layer, at least one of said plurality of layers and at least one of said magnetic shield layers having a same material.

2. (Cancelled)

3. (Original) The magnetic non-volatile memory device according to claim 1, said device characterized in that:

said magnetic shield layer is formed of a nano granular structure having a magnetic layer and a non-magnetic layer.

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4. (Original) The magnetic non-volatile memory device according to claim 1, said device characterized in that:

said magnetic shield layer has a composing element which is common to a part of an element of various layers composing said device.

5. (Original) The magnetic non-volatile memory device according to claim 1, said device characterized in that:

a passivation film is formed on said magnetic shield layer.

6. (Previously Presented) The magnetic non-volatile memory device according to claim 1, said device characterized in that:

said magnetic shield layers formed on a device surface at the mounting side of said device, and a device surface opposite to said mounting side of said device, are magnetically coupled with each other.

7. (Previously Presented) The magnetic non-volatile memory device according to claim 4, said device characterized in that:

said composing element includes one selected from the group consisting of Fe, Co, Pt,

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Mn, and Al.

8. (Currently Amended) A method for manufacturing a magnetic non-volatile memory device provided with a magnetic shielding structure for suppressing the influence of external magnetic fields, said method characterized in that:

various layers formed in said device, and a magnetic shield layer formed on a surface at top and bottom regions of said device for suppressing penetration of magnetic flux into said device are formed in a single sputtering chamber and a target used in forming at least one of the shield layers is the same as a target for forming a layer located between the magnetic shield layers.